

Features

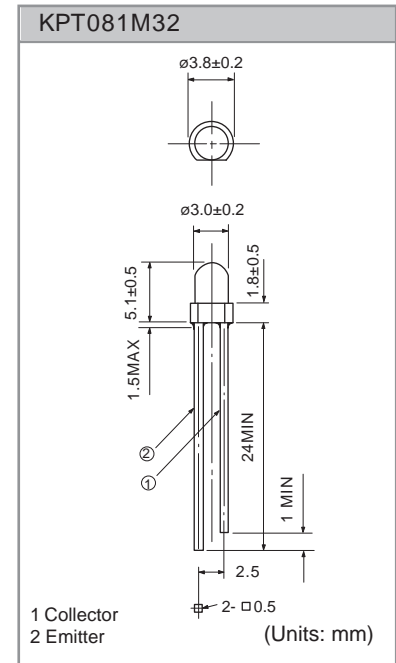
- NPN phototransistor
- Transparent epoxy potting
- Low leak current

Applications

- Optical switches
- Optical encoders
- Photo-isolator
- Camera stroboscopes
- Infrared sensors
- Automatic control apparatus

Maximum ratings

Item	Symbol	Value	Units
Collector •Emitter V ol.	V_{ceo}	20	V
Emitter •Collector V ol.	V_{eco}	5	V
Collector •Base Vol.	V_{cbo}	-	V
Emitter •Base Vol.	V_{ebo}	-	V
Collector Dissipation	P_o	75	mW
Operating Temperature	T_{opr}	-25 ~ + 85	°C
Storage Temperature	T_{stg}	-30 ~ +100	°C



Characteristics (T_a=25 °C unless otherwise noted.)

Parameter	Symbol	Min.	Typ.	Max.	Units	Test Conditions
Active area	S		0.64x0.64		mm	
Sensitive Wavelength		400	880(ρ)	1000	nm	ρ = Peak wavelength
Photocurrent	I_L		4		mA	$V_{ce}=5V$, 1000lux(@2856K)
Dark Current	I_{ceo}		5	200	nA	$V_{ce}=20V$
Current Amplification Factor	h_{FE}	600				$V_{ce}=5V$, $I_c=2mA$
Collector•Emitter Saturation Voltage	$V_{ce(sat)}$			0.4	V	$I_c=1 mA$, 1000lux(@2856K)
Rise/Fall Time	t_r, t_f		5		μs	$V_{ce} = 5V$, $I_c=2mA$, $R_L=100\Omega$
Half angle	θ		±45			deg.